NSN 5962-01-365-5109

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View Online at https://aerobasegroup.com/nsn/5962-01-365-5109

Between 1.430 inches and 1.485 inches

Body Width:

Between 0.245 inches and 0.310 inches

Body Height:

Between 0.155 inches and 0.200 inches

Maximum Power Dissipation Rating:

1.0 watts

Operating Tempurature Range:

-55.0/+125.0 degrees celsius

Storage Tempurature Range:

-65.0/+150.0 degrees celsius

End Application:

1430-01-087-6330

Inclosure Material:

Ceramic

Inclosure Configuration:

Dual-in-line

Output Logic Form:

Complementary-metal oxide-semiconductor logic

Current Rating Per Characteristic:

20.00 milliamperes average forward current averaged over a full 60-hz cycle not applicable

Terminal Surface Treatment:

Solder

Product Name:

Microcircuit, digital, cmos, 2k x 9 first-in first-out, monolithic silcon

Voltage Rating And Type Per Characteristic:

-0.5 volts applied and 7.0 volts applied

Time Rating Per Chacteristic:

30.00 nanoseconds af output megawatts

Memory Device Type:

First-in first-out

Hybrid Technology Type:

Monolithic

Test Data Document:

67268-5962-88669 standard (includes industry or association standards, individual manufactureer standards, etc.).

Terminal Type And Quantity:

28 printed circuit

Specification Data:

96906-mil-std-883 government standard

Shelf Life:

N/a

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Demilitarization:

No

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